



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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TECHNOLOGY CENTER 2800

Applicant: Nakajima et al.
Appl. No.: 10/071,909
Filed: February 7, 2002
Title: DISPLAY SYSTEM AND METHOD OF PRODUCING THE SAME
Art Unit: 2814
Examiner: D. Wille
Docket No.: 112857-317

Assistant Commissioner for Patents
Washington, DC 20231

RESPONSE TO OFFICE ACTION

Sir:

In response to the Office Action mailed January 30, 2003, please amend the above-identified application as follows:

In the Specification:

Please amend the paragraph beginning on page 13, line 3 as follows:

The semiconductor light-emitting device is not particularly limited as to the method of producing the same, constitution of materials or crystal structure, as far as the conductor film is formed on an upper end portion thereof exposed by thinning the insulation layer covering it and the upper end portion electrode is led out to the upper surface of the insulation layer. Namely, the semiconductor light-emitting device may be a minute semiconductor chip, for example, of 300 μm in size diced from a compound semiconductor wafer being a raw material of a light-emitting diode or a semiconductor laser, or an extremely minute semiconductor of 10 to 100 μm in size selectively crystal-grown on a substrate for growth such as sapphire.